1.5V Drive Nch MOSFET RUR040N02

Structure

Silicon N-channel MOSFET

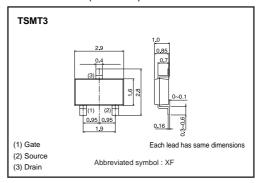
Features

- 1) 1.5V drive
- 2) Low On-resistance.
- 3) Built-in G-S Protection Diode.
- 4) Small Surface Mount Package (TSMT3).

Application

Switching

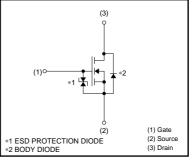
•Dimensions (Unit : mm)



Packaging specifications

	Package	Taping	
Туре	Code	TL	
	Basic ordering unit (pieces)	3000	
RUR040N0	0		

•Equivalent circuit



Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit		
Drain-source voltage		VDSS	20	V		
Gate-source voltage		Vgss	±10	V		
Drain autrent	Continuous	ID	±4.0	A		
Drain current	Pulsed	IDP *1	±8.0	A		
Source current	Continuous	ls	0.8	A		
(Body diode)	Pulsed	Isp *1	8.0	А		
Total power dissipation		P _D *2	1.0	W		
Channel temperature		Tch	150	٥C		
Range of storage temperature		Tstg	-55 to +150	°C		

*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	125	°C / W
* Mounted on a ceramic board			

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•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
ate-source leakage	Igss	-	-	±10	μΑ	V _{GS} =±10V, V _{DS} =0V	
rain-source breakdown voltage	V(BR) DSS	20	-	-	V	I _D =1mA, V _{GS} =0V	
ero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} =20V, V _{GS} =0V	
ate threshold voltage	VGS (th)	0.3	-	1.3	V	Vos=10V, Io=1mA	
	RDS (on)*	-	25	35	mΩ	I _D =4.0A, V _{GS} =4.5V	
atic drain-source on-state		-	33	46	mΩ	I _D =4.0A, V _{GS} =2.5V	
resistance		-	42	59	mΩ	I _D =2.0A, V _{GS} =1.8V	
		-	55	110	mΩ	I _D =0.8A, V _{GS} =1.5V	
orward transfer admittance	Y _{fs} *	5.0	-	-	S	V _{DS} =10V, I _D =4.0A	
out capacitance	Ciss	-	680	_	pF	V _{DS} =10V	
utput capacitance	Coss	_	150	-	pF	V _{GS} =0V	
everse transfer capacitance	Crss	-	90	_	pF	f=1MHz	
rn-on delay time	td (on) *	-	10	-	ns	ID=2.0A, VDD≒10V VGs=4.5V RL≒5Ω, RG=10Ω	
se time	tr *	-	30	-	ns		
Irn-off delay time	t _{d (off)} *	-	50	-	ns		
II time	tr *	-	60	-	ns		
otal gate charge	Qg *	_	8	-	nC	I _D =4.0A, V _{DD} ≒10V V _{GS} =4.5V	
ate-source charge	Q _{gs} *	-	1.8	-	nC		
te-drain charge	Q _{gd} *	_	1.3	-	nC	R∟≒2.5Ω, R _G =10Ω	

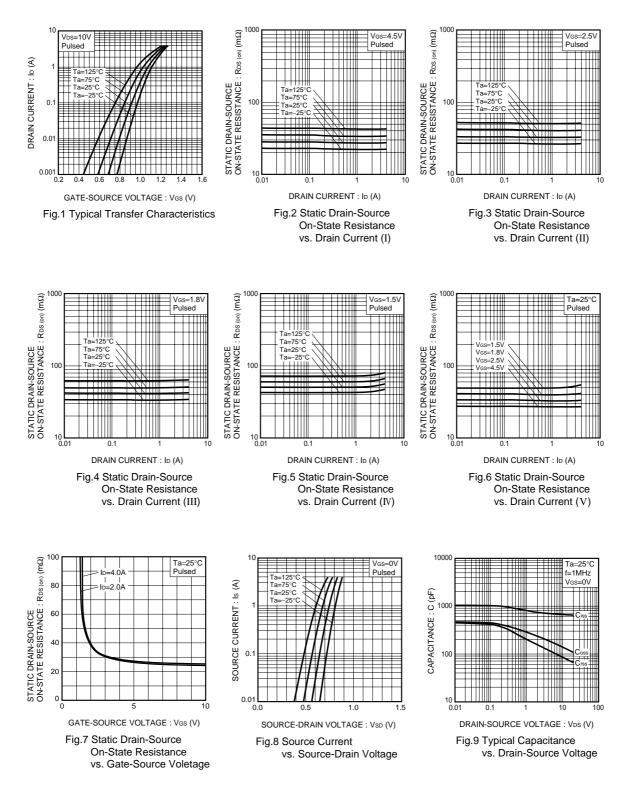
•Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	1.2	V	Is=0.8A, V _{GS} =0V
Dulaad						

*Pulsed

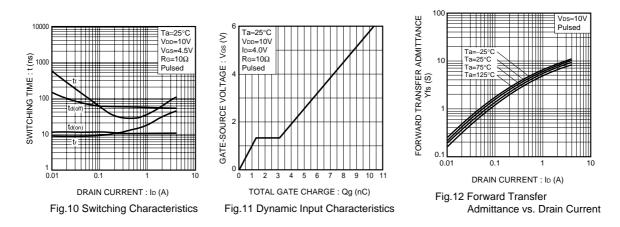
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Electrical characteristic curves



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Measurement circuits

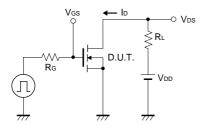


Fig.13 Switching Time Test Circuit

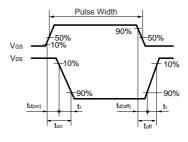


Fig.14 Switching Time Waveforms

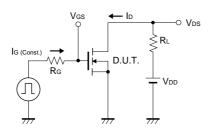


Fig.15 Gate Charge Test Circuit

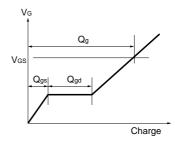


Fig.16 Gate Charge Waveform

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Appendix1-Rev2.0

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